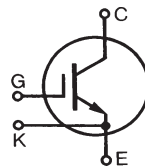


## GenX3™ A3-Class IGBTs

**IXGK120N60A3**  
**IXGX120N60A3**

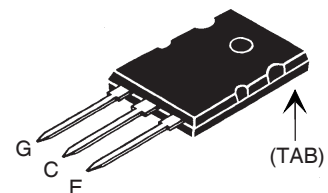
**$V_{CES} = 600V$**   
 **$I_{C110} = 120A$**   
 **$V_{CE(sat)} \leq 1.35V$**

Ultra-Low  $V_{sat}$  PT IGBTs for  
up to 5kHz Switching

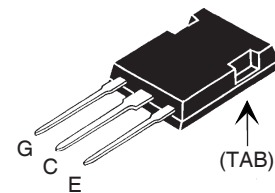


Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $150^\circ C$	600	V
$V_{CGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GE} = 1M\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$	200	A
$I_{C110}$	$T_C = 110^\circ C$	120	A
$I_{LRMS}$	Terminal Current Limit	75	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	600	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 125^\circ C$ , $R_G = 1.5\Omega$ Clamped Inductive Load	$I_{CM} = 200$ @ $\leq 600$	A V
$P_c$	$T_C = 25^\circ C$	780	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062 in.) from Case for 10	260	$^\circ C$
$M_d$	Mounting Torque ( IXGK )	1.13/10	Nm/lb.in.
$F_c$	Mounting Force ( IXGX )	20..120/4.5..27	N/lb.
<b>Weight</b>	TO-264	10	g
	PLUS247	6	g

TO-264 (IXGK)



PLUS 247™ (IXGX)



G = Gate                      E = Emitter  
C = Collector                TAB = Collector

### Features

- Optimized for Low Conduction Losses
- Square RBSOA
- High Current Handling Capability
- International Standard Packages

### Advantages

- High Power Density
- Low Gate Drive Requirement

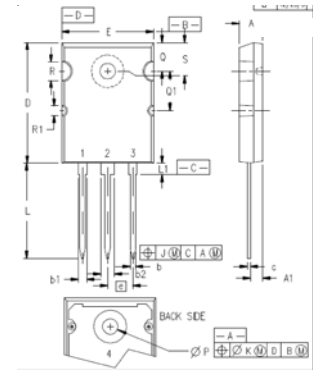
### Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- Inrush Current Protection Circuits

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{GE(th)}$	$I_C = 500\mu A$ , $V_{CE} = V_{GE}$	3.0		5.0 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 125^\circ C$			50 $\mu A$ 1.25 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 400$ nA
$V_{CE(sat)}$	$I_C = 100A$ , $V_{GE} = 15V$ , Note 1		1.20	1.35 V

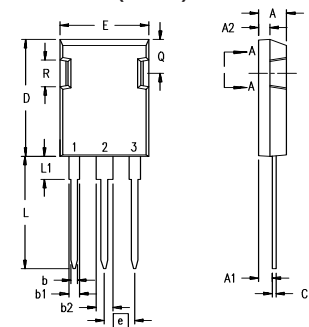
Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 60A, V_{CE} = 10V$ , Note 1	65	108	S
$C_{ies}$	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$		14.8	nF
$C_{oes}$			800	pF
$C_{res}$			140	pF
$Q_{g(on)}$	$I_C = I_{C110}, V_{GE} = 15V, V_{CE} = 0.5 \cdot V_{CES}$		450	nC
$Q_{ge}$			67	nC
$Q_{gc}$			130	nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ C</math></b> $I_C = 100A, V_{GE} = 15V$ $V_{CE} = 480V, R_G = 1.5\Omega$		39	ns
$t_{ri}$			82	ns
$E_{on}$			2.7	mJ
$t_{d(off)}$			295	ns
$t_{fi}$			260	ns
$E_{off}$			6.6	mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 125^\circ C</math></b> $I_C = 100A, V_{GE} = 15V$ $V_{CE} = 480V, R_G = 1.5\Omega$		40	ns
$t_{ri}$			83	ns
$E_{on}$			3.5	mJ
$t_{d(off)}$			420	ns
$t_{fi}$			410	ns
$E_{off}$			10.4	mJ
$R_{thJC}$			0.16	$^\circ C/W$
$R_{thCK}$		0.15		$^\circ C/W$

### TO-264 (IXGK) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
$\varnothing P$	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
$\varnothing R$	.155	.187	3.94	4.75
$\varnothing R1$	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

### PLUS 247™ (IXGX) Outline



Terminals: 1 - Gate  
2 - Drain (Collector)  
3 - Source (Emitter)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A <sub>1</sub>	2.29	2.54	.090	.100
A <sub>2</sub>	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b <sub>1</sub>	1.91	2.13	.075	.084
b <sub>2</sub>	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244

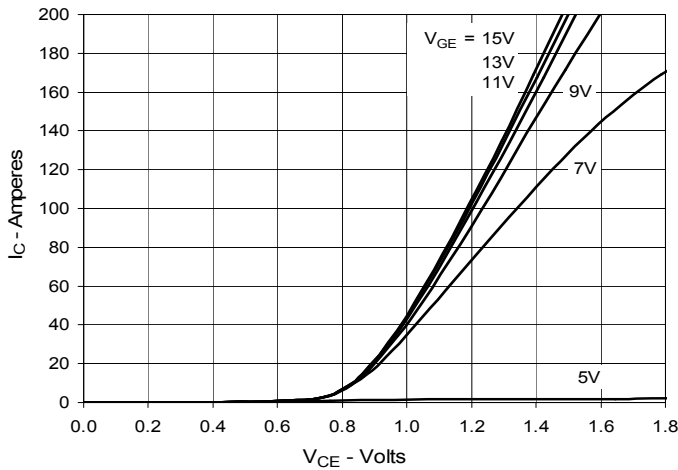
Note: 1. Pulse Test,  $t \leq 300\mu s$ ; Duty Cycle,  $d \leq 2\%$ .

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

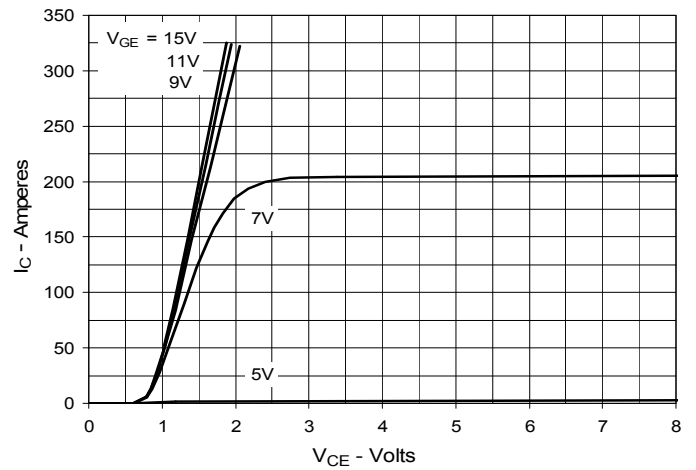
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

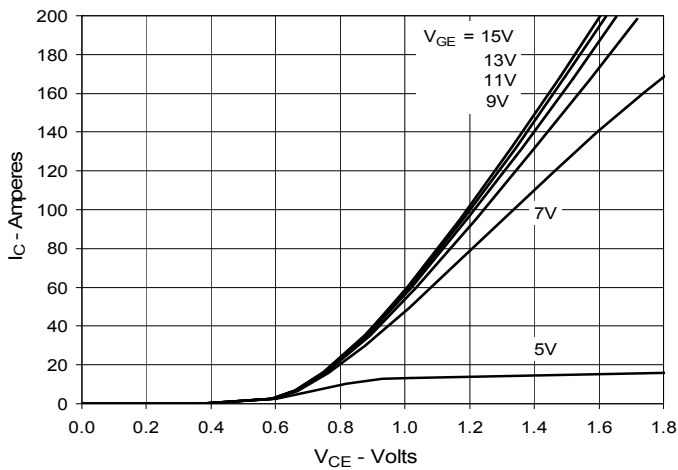
**Fig. 1. Output Characteristics @ 25°C**



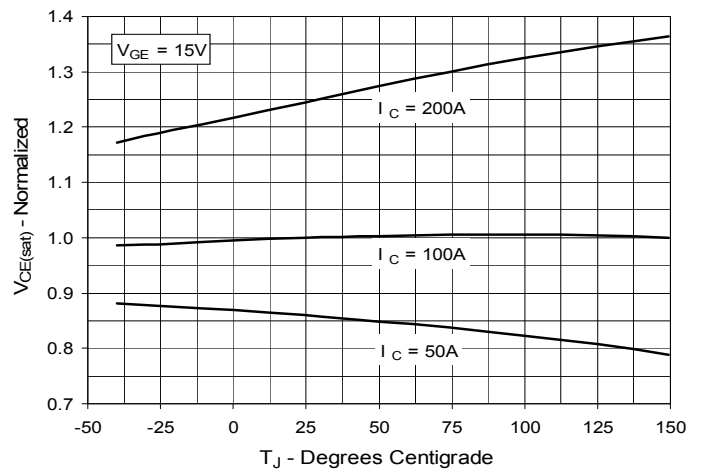
**Fig. 2. Extended Output Characteristics @ 25°C**



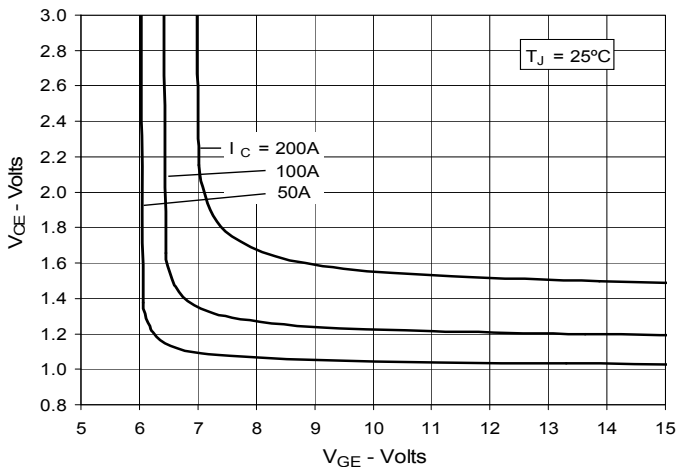
**Fig. 3. Output Characteristics @ 125°C**



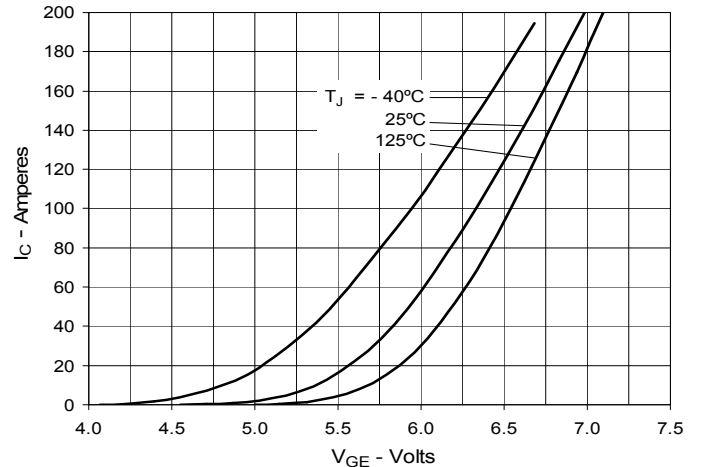
**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**



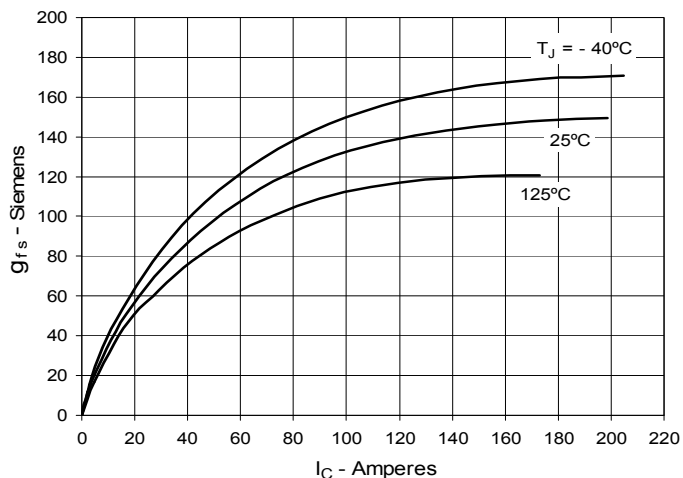
**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**



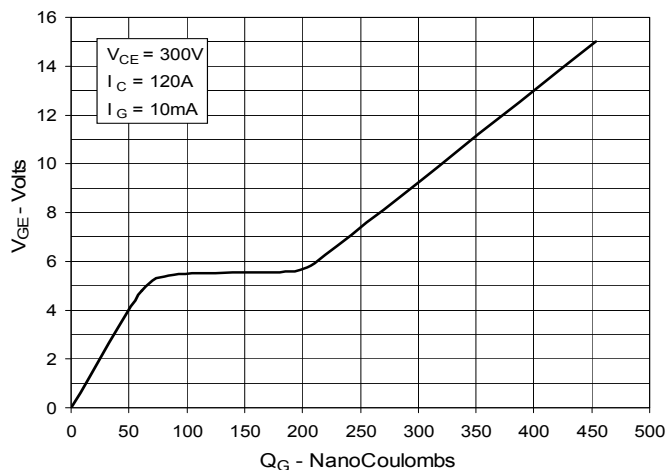
**Fig. 6. Input Admittance**



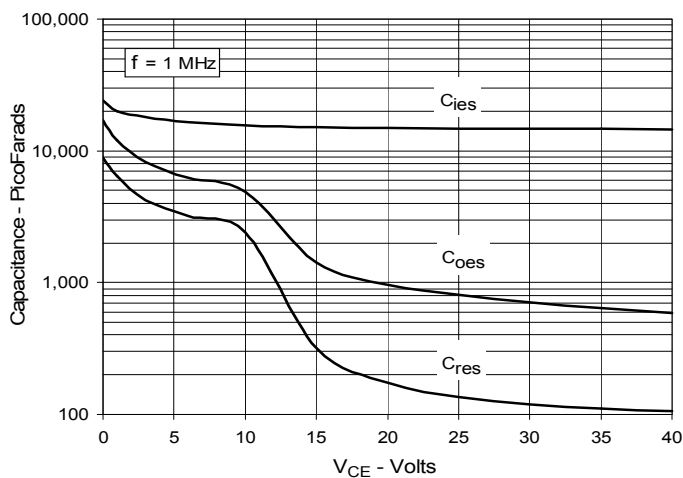
**Fig. 7. Transconductance**



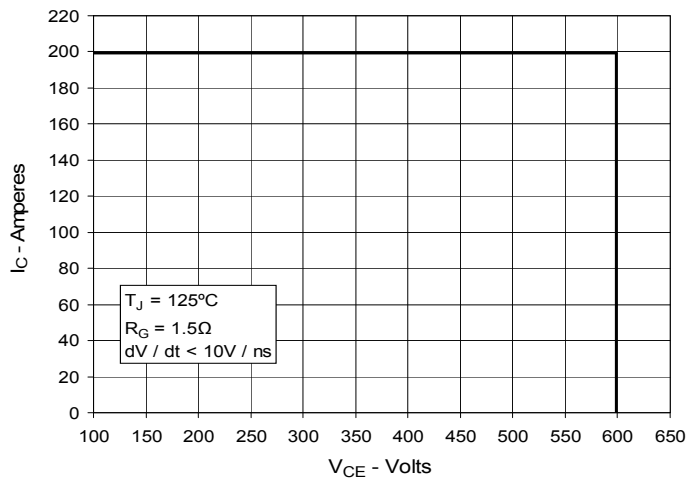
**Fig. 8. Gate Charge**



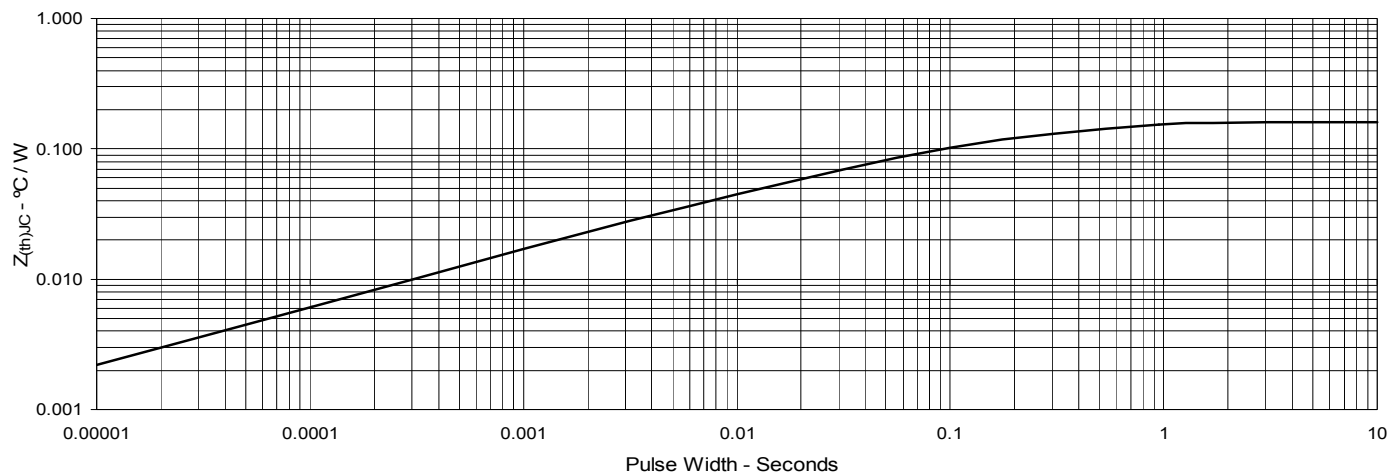
**Fig. 9. Capacitance**



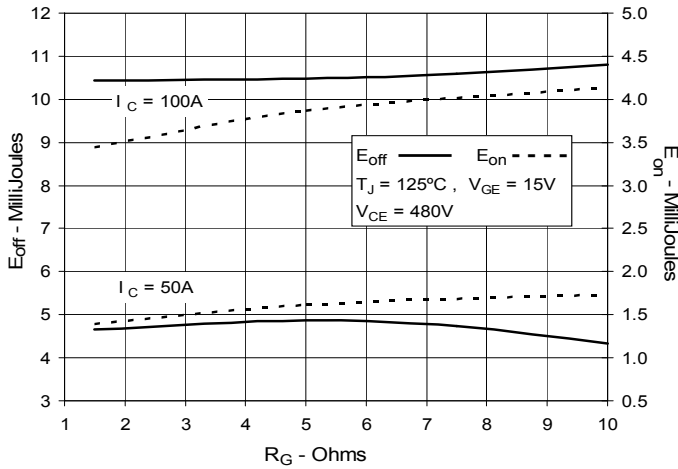
**Fig. 10. Reverse-Bias Safe Operating Area**



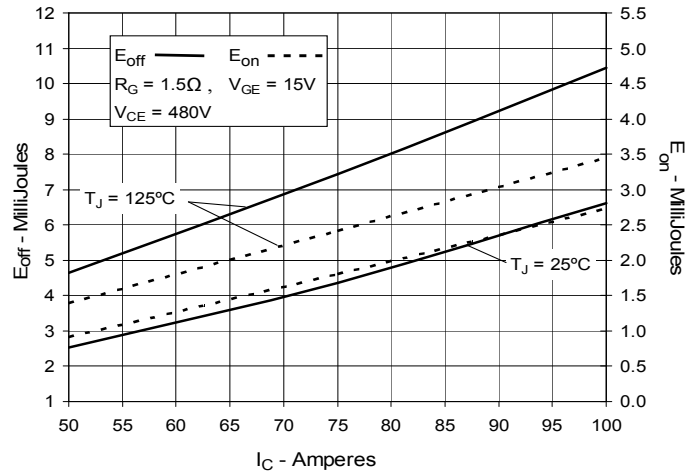
**Fig. 11. Maximum Transient Thermal Impedance**



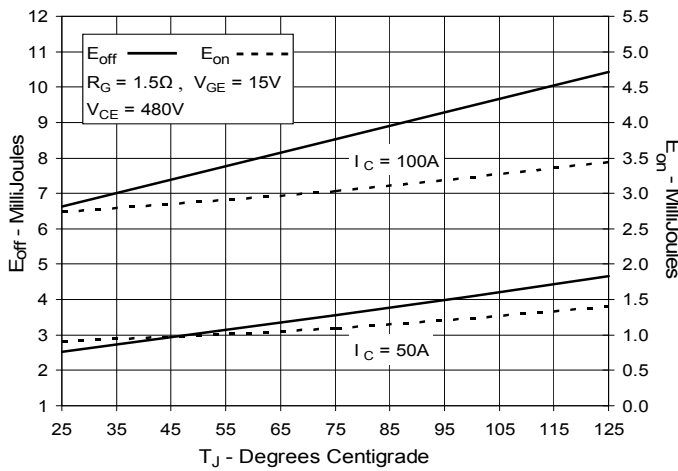
**Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance**



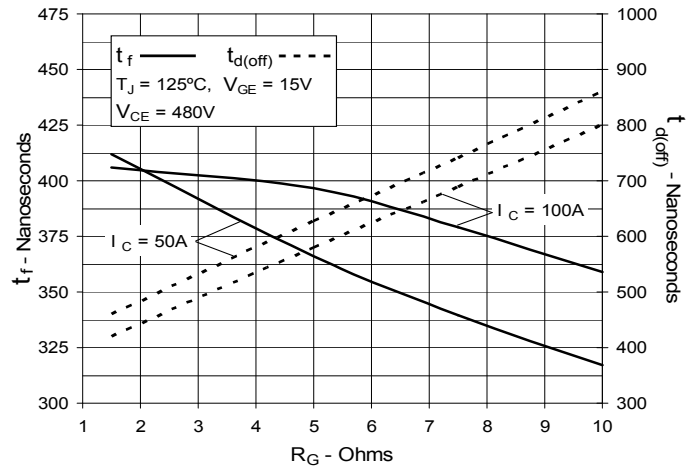
**Fig. 13. Inductive Switching Energy Loss vs. Collector Current**



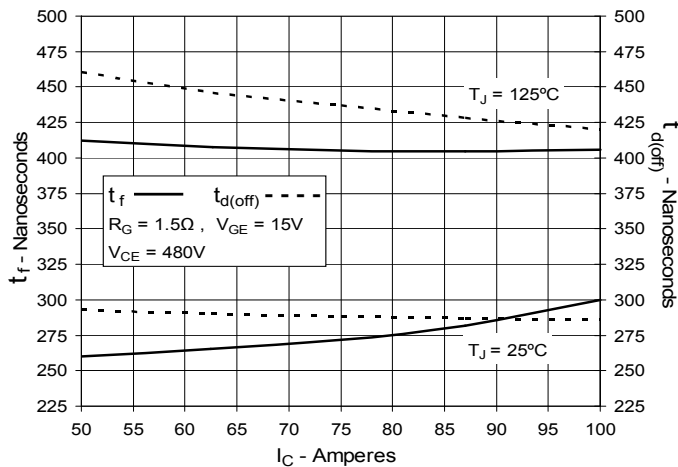
**Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature**



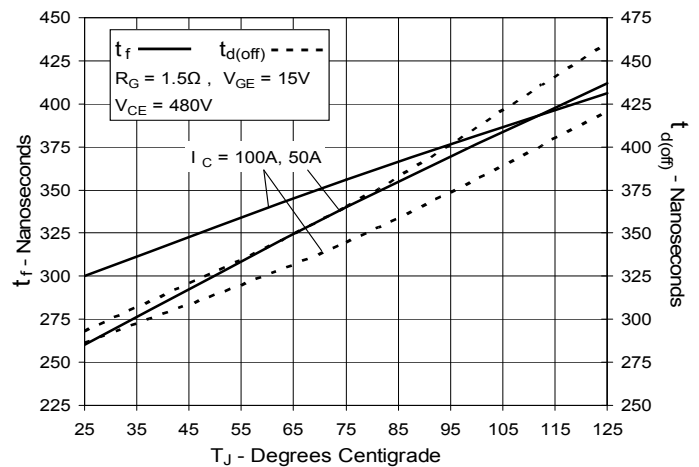
**Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance**



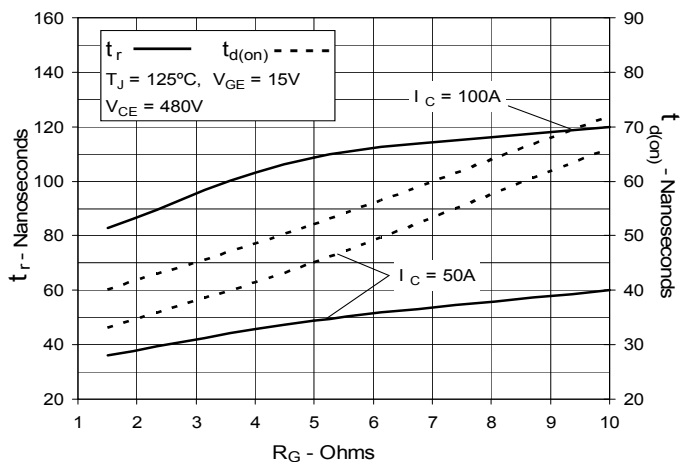
**Fig. 16. Inductive Turn-off Switching Times vs. Collector Current**



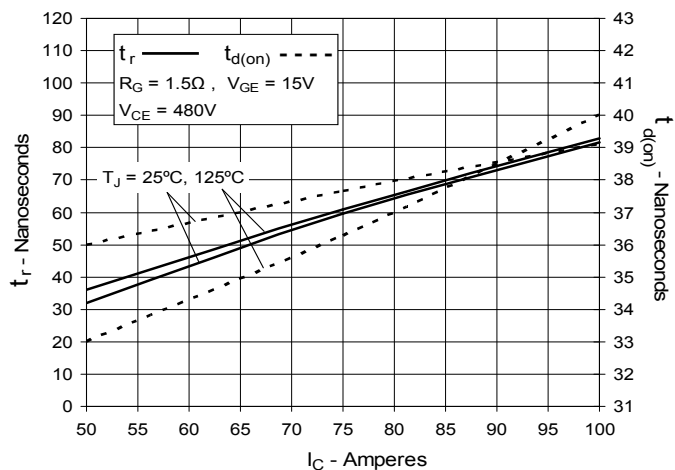
**Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature**



**Fig. 18. Inductive Turn-on  
Switching Times vs. Gate Resistance**



**Fig. 19. Inductive Turn-on  
Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-on  
Switching Times vs. Junction Temperature**

